

# **BUK954R8-60E**

## N-channel TrenchMOS logic level FET

11 September 2012

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

Logic level N-channel MOSFET in a SOT78 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with VGS(th) rating of greater than 0.5V at 175 °C

## 1.3 Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	234	W
Static charac	teristics						,
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	4	4.9	mΩ
Dynamic cha	racteristics						,
$Q_{GD}$	gate-drain charge	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 48 V; Fig. 13; Fig. 14		-	20.3	-	nC

[1] Continuous current is limited by package.



N-channel TrenchMOS logic level FET

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain	$1 \qquad 7 \qquad 7$	
3	S	source		G C
mb	D	mounting base; connected to drain		mbb076 S
			TO-220AB (SOT78A)	

## 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK954R8-60E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A			

## 4. Limiting values

Table 4. Limiting values

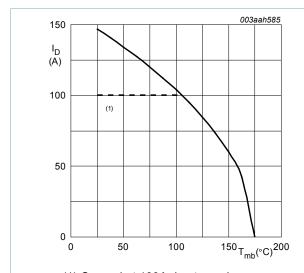
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	60	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$		-	60	V
$V_{GS}$	gate-source voltage	T <sub>j</sub> ≤ 175 °C; Pulsed	[1][2]	-15	15	V
		T <sub>j</sub> ≤ 175 °C; DC		-10	10	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 1</u>	[3]	-	100	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 1</u>	[3]	-	100	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 4		-	590	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	234	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
Is	source current	T <sub>mb</sub> = 25 °C	[3]	-	100	Α
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Symbol	Parameter	Conditions		Min	Max	Unit
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	590	Α
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 100 A; $V_{sup} \le$ 60 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[4][5]	-	273	mJ

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering T<sub>i</sub> and or V<sub>GS</sub>
- [3] Continuous current is limited by package.
- [4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [5] Refer to application note AN10273 for further information.



(1) Capped at 100A due to package

Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

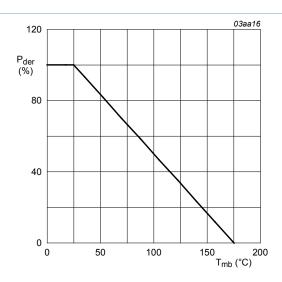


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \,\%$$

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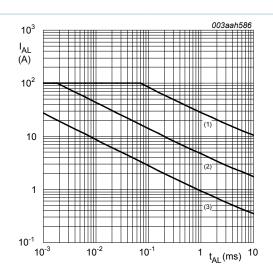
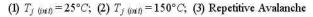


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



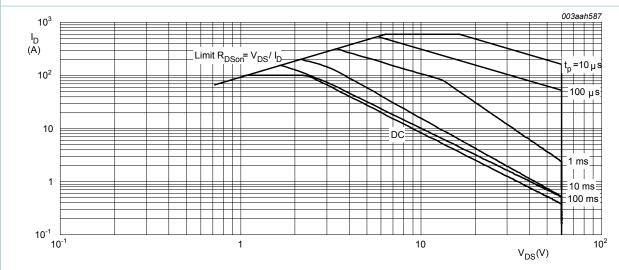


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

#### 5. Thermal characteristics

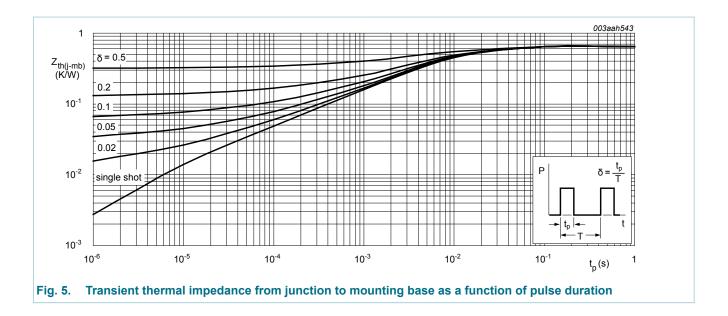
Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	_	_	0.64	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

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### 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
	breakdown voltage	$I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = -55 °C	54	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; Fig. 9	0.5	-	-	V
I <sub>DSS</sub> drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.05	1	μΑ	
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub> gate leakage current	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA	
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	4	4.9	mΩ
	resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 11	-	3.6	4.5	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	-	10.8	mΩ
Dynamic ch	naracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 5 V;	-	65	-	nC
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14	-	17.5	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$Q_{GD}$	gate-drain charge		-	20.3	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	7282	9710	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	607	729	pF
C <sub>rss</sub>	reverse transfer capacitance		-	313	429	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 45 V; $R_L$ = 1.8 $\Omega$ ; $V_{GS}$ = 5 V;	-	36	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	73	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	78	-	ns
t <sub>f</sub>	fall time		-	68	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to center of die ; $T_j = 25 ^{\circ}\text{C}$	-	2.5	-	nΗ
		from drain lead 6mm from package to centre of die ; $T_j$ = 25 °C	-	4.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bonding pad ; $T_j$ = 25 °C	-	7.5	-	nΗ
Source-dra	nin diode			1		,
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	39	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V	-	56	-	nC

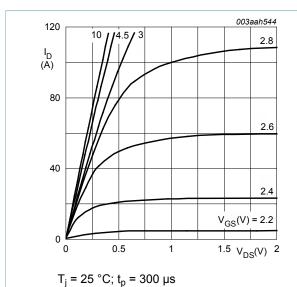


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

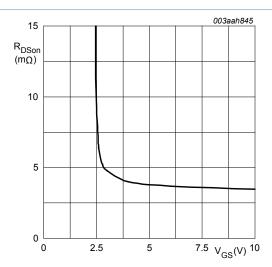


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

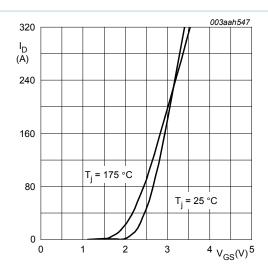


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



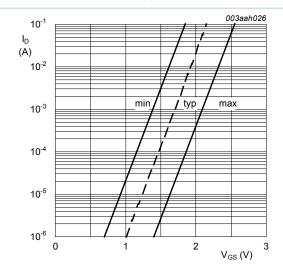


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C;  $V_{DS} = 5V$ 

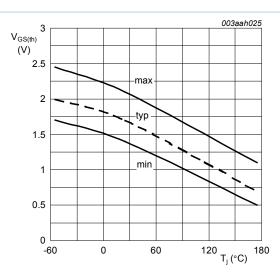
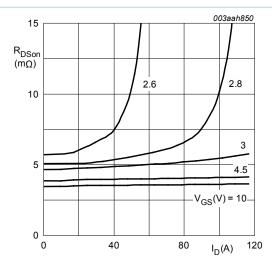


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1$$
 mA;  $V_{DS} = V_{GS}$ 



 $T_i$  = 25 °C;  $t_p$  = 300  $\mu$ s

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

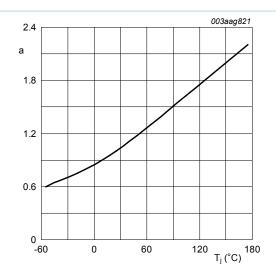


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

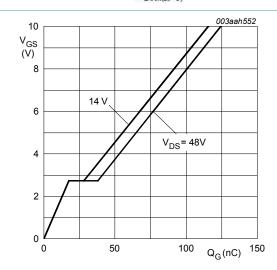


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

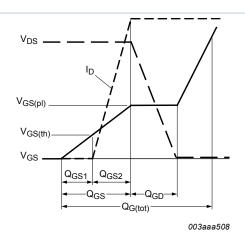


Fig. 13. Gate charge waveform definitions

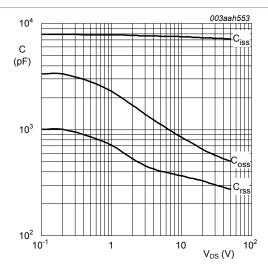


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; f = \mathbf{1}MHz$$

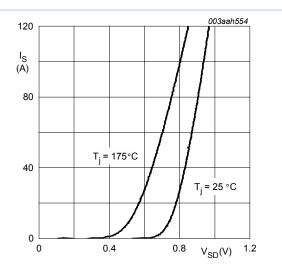
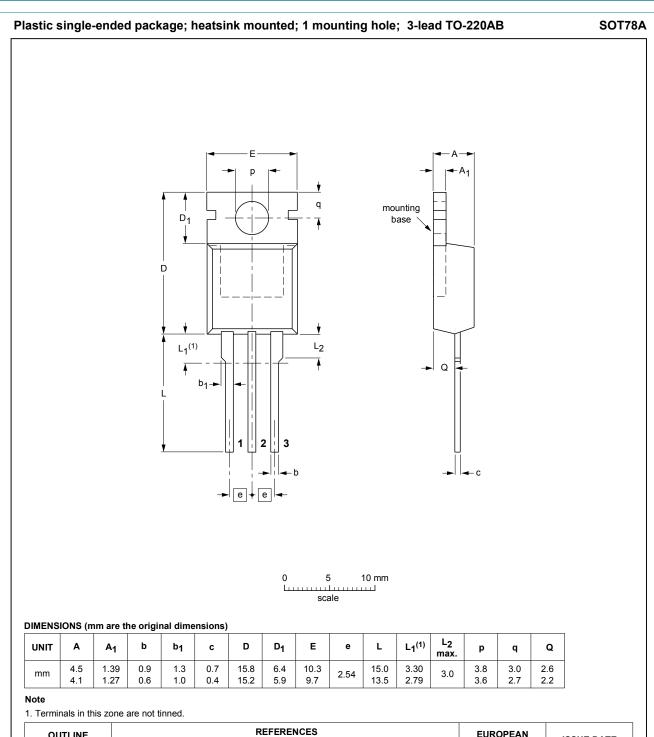


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

## 7. Package outline



OUTLINE REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78A		3-lead TO-220AB	SC-46		<del>-03-01-22-</del> 05-03-14

Fig. 17. Package outline TO-220AB (SOT78A)

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#### N-channel TrenchMOS logic level FET

#### 9. Contents

1	Product profile	1
1.1	General description	
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	4
6	Characteristics	5
7	Package outline	10
8	Legal information	11
8.1	Data sheet status	11
8.2	Definitions	11
8.3	Disclaimers	11

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